

a first current blocking layer formed on said flat portion and on sidewalls of said ridge portion of said cladding layer and composed of a high-resistive nitride based semiconductor containing impurities;

wherein the cladding layer is composed of AlGa<sub>N</sub>; and

wherein the first current blocking layer is composed of AlGa<sub>N</sub> having a larger Al composition ratio than that of the cladding layer.

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10. (Amended) A semiconductor light emitting device comprising:

an active layer composed of a nitride based semiconductor;

a cladding layer formed on said active layer, composed of a nitride based semiconductor of a first conductivity type, and having a flat portion and a ridge portion formed on the flat portion, said cladding layer having a recess on said flat portion along both sidewalls of said ridge portion; and

a first current blocking layer formed on said flat portion and on the sidewalls of said ridge portion such that it is embedded in said recess of said cladding layer;

wherein the cladding layer is composed of AlGa<sub>N</sub>; and

wherein the first current blocking layer is composed of AlGa<sub>N</sub> having a larger Al composition ratio than that of the cladding layer.

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